# DDR3 Synchronous DRAM Memory

- DDR data transfer
- Burst read and write
- Simultaneous multiple bank operation
- Command sequencing and pipelining
- Read/Write leveling



Figure 4: 256 Meg x 8 Functional Block Diagram

## 8-bit prefetch/burst length



## Commands

### PRECHARGE

Ready BANK for an ACTIVATE (closes currently active row)

⇒ Read and Write may issue an auto-precharge

#### ♦ ACTIVATE

⇔ Open a ROW in a BANK for access (Row Address)

⇒ ROW remains active until a Precharge

#### ♦ READ

⇒ Initiate a burst read from an active ROW in a BANK

## ♦ WRITE

⇔ Initiate a burst write to an active ROW in a BANK

## ✦ REFRESH/SELF REFRESH

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#### Figure 2: Simplified State Diagram



## Reads

#### Figure 67: READ Latency





Figure 68: Consecutive READ Bursts (BL8)

[\*\*] Transitioning Data [//] Don't Care



Figure 85: Consecutive WRITE (BL8) to WRITE (BL8)



#### Commands - Truth Tables

#### Table 69: Truth Table - Command

Notes 1–5 apply to the entire table

			CKE											
			Prev.	Next	]				BA				A[11,	
Function		Symbol	Cycle	Cycle	CS#	RAS#	CAS#	WE#	[2:0]	An	A12	A10	9:0]	Notes
MODE REGISTER SET		MRS	Н	Н	L	L	L	L	BA	OP code				
REFRESH		REF	Н	Н	L	L	L	Н	v	v	v	v	v	
Self refresh entry		SRE	Н	L	L	L	L	Н	v	v	v	v	v	6
Self refresh exit		SRX	L	Н	Н	V	v	V	V	v	v	v	v	6,7
					L	Н	Н	Н						
Single-bank PRECHARGE		PRE	Н	Н	L	L	Н	L	BA	v	V	L	v	
PRECHARGE all banks		PREA	Н	Н	L	L	Н	L	V		v	Н	v	
Bank ACTIVATE		ACT	Н	Н	L	L	Н	Н	BA	Row address (RA)				
WRITE	BL8MRS, BC4MRS	WR	Н	Н	L	Н	L	L	BA	RFU	v	L	CA	8
	BC4OTF	WRS4	Н	Н	L	Н	L	L	BA	RFU	L	L	CA	8
	BL8OTF	WRS8	Н	Н	L	Н	L	L	BA	RFU	Н	L	CA	8
WRITE with auto precharge	BL8MRS, BC4MRS	WRAP	Н	Н	L	н	L	L	BA	RFU	V	н	CA	8
	BC4OTF	WRAPS4	Н	Н	L	Н	L	L	BA	RFU	L	Н	CA	8
	BL8OTF	WRAPS8	Н	Н	L	Н	L	L	BA	RFU	Н	Н	CA	8
READ	BL8MRS, BC4MRS	RD	Н	Н	L	Н	L	н	BA	RFU	v	L	CA	8
	BC4OTF	RDS4	Н	Н	L	Н	L	Н	BA	RFU	L	L	CA	8
	BL8OTF	RDS8	Н	Н	L	Н	L	Н	BA	RFU	Н	L	CA	8
READ with auto precharge	BL8MRS, BC4MRS	RDAP	Н	Н	L	Н	L	Н	BA	RFU	v	Н	CA	8
	BC4OTF	RDAPS4	Н	Н	L	Н	L	Н	BA	RFU	L	Н	CA	8
	BL8OTF	RDAPS8	Н	Н	L	Н	L	Н	BA	RFU	Н	Н	CA	8
NO OPERATION		NOP	Н	Н		Н	Н	Н	V	V	v	V	v	9
Device DESELECTED		DES	Н	Н	Н	X	Х	X	X	Х	Х	X	X	10
Power-down entry		PDE	Н	L	L	Н	Н	Н	V	V	V	V	v	6
					Н	V	V	V						
Power-down exit		PDX	L	Н	L	Н	Н	Н	V	V	V	v	V	6, 11
					Н	v	v	V						
ZQ CALIBRATION LONG		ZQCL	Н	Н	L	Н	Н	L	Х	Х	Х	Н	Х	12
ZQ CALIBRATION SHORT		ZQCS	Н	Н	L	Н	Н	L	Х	Х	Х	L	Х	

## Mode Registers

### Burst length: 4/8/dynamic

### ✦ READ burst type: Sequential/Interleaved

8	READ	0 0 0	0, 1, 2, 3, 4, 5, 6, 7	0, 1, 2, 3, 4, 5, 6, 7	1
		0 0 1	1, 2, 3, 0, 5, 6, 7, 4	1, 0, 3, 2, 5, 4, 7, 6	1
		010	2, 3, 0, 1, 6, 7, 4, 5	2, 3, 0, 1, 6, 7, 4, 5	1
		011	3, 0, 1, 2, 7, 4, 5, 6	3, 2, 1, 0, 7, 6, 5, 4	1
		100	4, 5, 6, 7, 0, 1, 2, 3	4, 5, 6, 7, 0, 1, 2, 3	1
		101	5, 6, 7, 4, 1, 2, 3, 0	5, 4, 7, 6, 1, 0, 3, 2	1
		110	6, 7, 4, 5, 2, 3, 0, 1	6, 7, 4, 5, 2, 3, 0, 1	1
		111	7, 4, 5, 6, 3, 0, 1, 2	7, 6, 5, 4, 3, 2, 1, 0	1
	WRITE	V V V	0, 1, 2, 3, 4, 5, 6, 7	0, 1, 2, 3, 4, 5, 6, 7	1, 3

#### ♦ Write Recovery: clock cycles

## Mode Registers (cont)

#### CAS Read Latency: clock cycles READ to data output





## Mode Registers (cont)

#### ♦ Additive Latency

- Allows ACTIVATE − READ/WRITE to be done together
- ◇ AL holds back READ/WRITE for n clock cycles

## Mode Registers (cont)

#### ♦ CAS Write Latency

Figure 57: CAS Write Latency

BC4



## "Fly-by" clocking – Source Synchronous



# "Fly-by" and Read Leveling



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## Write-Leveling



Figure 1-7 Conceptual Diagram of Write Leveling

## Memory Bandwidth

Accesses to same row are fast
 Back-to-back reads/writes to row

- Changing rows costs time
   PRECHARGE/ACTIVATE
- Multiple bank accesses can be overlapped
  - ⇒ Interleave bank accesses
  - Pipeline/overlap PRECHARGE/ACTIVATE
  - ↔ Good for random access